

FIG. 2B – PRIOR ART

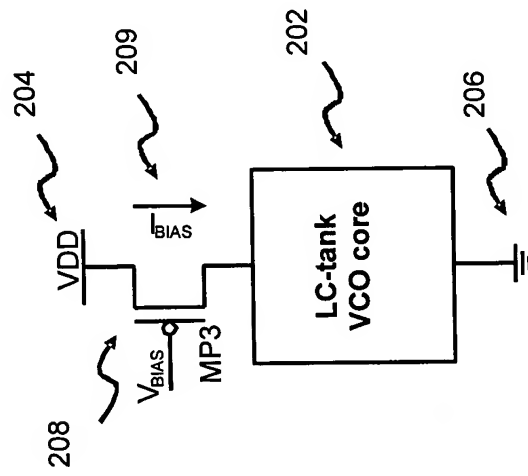
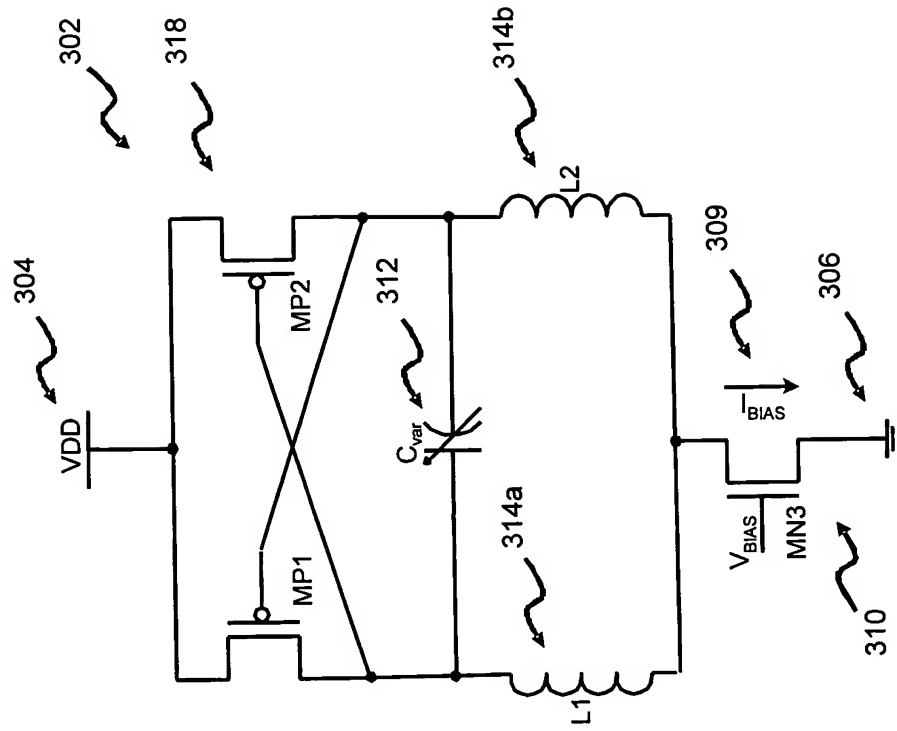
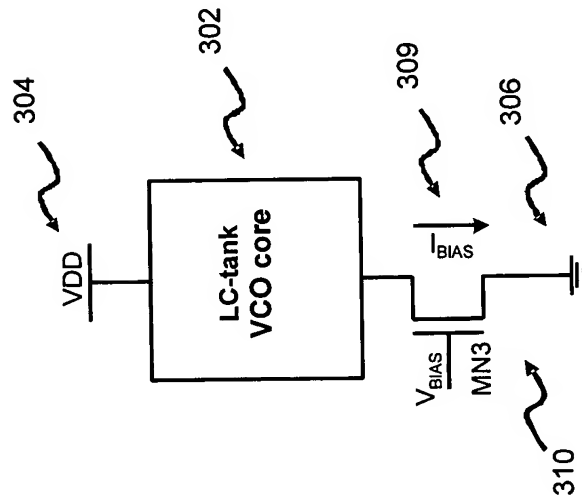


FIG. 2A – PRIOR ART



**FIG. 3B – PRIOR ART**



**FIG. 3A – PRIOR ART**





Parameters	Simulation Results					Unit
	Fig. 4B (proposed)	Fig 4 C (proposed)	Fig. 4D (proposed)	Fig.3 (prior art)	Fig. 2 (prior art)	
Center Frequency	2.632	2.625	2.784	2.594	3.337	GHz
Frequency Tuning Range	23.7	23.9	10.0	25.0	35.7	%
Phase Noise at 100KHz offset from Center Frequency	-103.0	-103.4	-97.8	-100.6	-75.7	dBc/Hz
Frequency Pushing	0.25	16.84	0.14	20.49	82.48	%/V
DC Power Current	4	4	4	4	4	mA
Power Supply	3	3	3	3	3	V

Table 1: Comparison of different configurations

Transistor Sizes		Frequency Pushing	Comment
Channel Length	Channel Width		
N/A	N/A	16.84%/V	Frequency Pushing is high
0.35μm	10*85.1μm	0.47%/V	Frequency Pushing is low and improves with increase in L
0.40μm	10*448μm	0.25%/V	
0.45μm	10*1576μm	0.15%/V	
0.50μm	10*3697μm	0.10%/V	

Table 2: Frequency Pushing vs. Channel Length of transistor MN3 in Fig. 4B. First row corresponds to Fig. 4C.

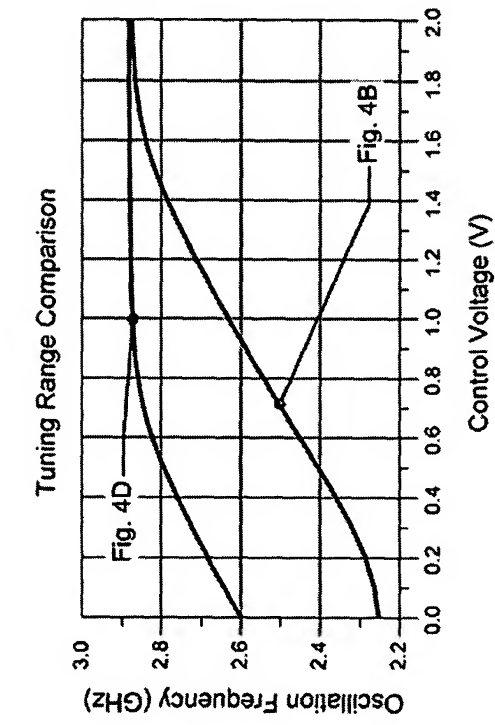


FIG. 5A

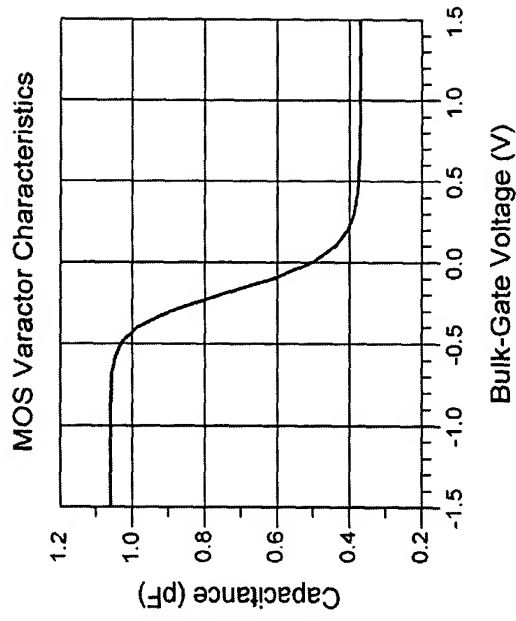


FIG. 5B